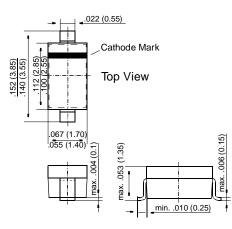
BAT42W, BAT43W

Schottky Diodes

<u>SOD-123</u>



Dimensions in inches and (millimeters)

FEATURES

For general purpose applications



- These diodes feature very low turnon voltage and fast switching. These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.
- These diodes are also available in the DO-35 case with the type designations BAT42 to BAT43 and in the MiniMELF case with type designations LL42 to LL43.

MECHANICAL DATA

Case: SOD-123 Plastic Case Weight: approx. 0.01 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	30	V
Forward Continuous Current at T _{amb} = 25 °C	IF	200	mA
Repetitive Peak Forward Current at $t_p < 1 \text{ s}$, $\delta < 0.5$, $T_{amb} = 25 \text{ °C}$	I _{FRM}	500	mA
Surge Forward Current at $t_p < 10$ ms, $T_{amb} = 25$ °C	I _{FSM}	4 ²⁾	A
Power Dissipation ¹⁾ at T _{amb} = 65 °C	P _{tot}	200 ²⁾	mW
Junction Temperature	Tj	125	°C
Ambient Operating Temperature Range	T _{amb}	-55 to +125	°C
Storage Temperature Range	T _S	-55 to +150	°C
²⁾ Valid provided that electrodes are kept at ambient tempe	erature		•



BAT42W, BAT43W

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Тур.	Max.	Unit
Reverse Breakdown Voltage tested with 100 μA Pulses	V _{(BR)R}	30	-	-	V
$\begin{array}{ll} \mbox{Forward Voltage} \\ \mbox{Pulse Test } t_p < 300 \ \mu s, \ \delta < 2\% \\ \mbox{at } I_F = 200 \ mA \\ \mbox{at } I_F = 10 \ mA \\ \mbox{at } I_F = 50 \ mA \\ \mbox{at } I_F = 50 \ mA \\ \mbox{at } I_F = 2 \ mA \\ \mbox{at } I_F = 15 \ mA \\ \mbox{BAT43W} \\ \mbox{BAT43W} \end{array}$	VF VF VF VF VF	- - - 0.26 -	- - - -	1 0.4 0.65 0.33 0.45	V V V V V
Leakage Current Pulse Test t _p < 300 μ s, δ < 2% at V _R = 25 V at V _R = 25 V, T _j = 100 °C	I _R I _R			0.5 100	μΑ μΑ
Capacitance at $V_R = 1 V$, f = 1 MHz	C _{tot}	_	7	_	pF
Reverse Recovery Time from I_F = 10 mA through I_R = 10 mA to I_R = 1 mA, R_L = 100 Ω	t _{rr}	-	-	5	ns
Detection Efficiency at $R_L = 15 \text{ K}\Omega$, $C_L = 300 \text{ pF}$, f = 45 MHz, $V_{RF} = 2 \text{ V}$	ην	80	_	-	%
Thermal Resistance Junction to Ambient Air	R _{thJA}	-	_	0.3 ²⁾	K/mW
²⁾ Valid provided that electrodes are kept at ambie	ent temperatur	e			

